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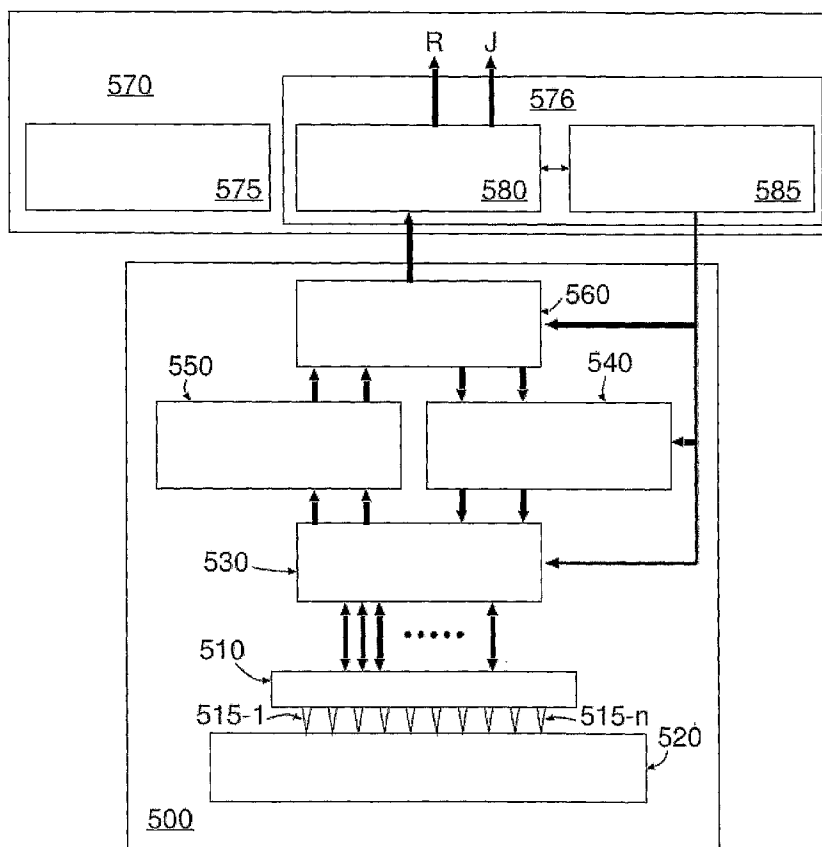
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(54) Title: METHOD FOR SHEET RESISTANCE AND LEAKAGE CURRENT DENSITY MEASUREMENTS ON SHALLOW SEMICONDUCTOR IMPLANTS



(57) Abstract: A method for accurately determining the sheet resistance and leakage current density of a shallow implant in a semiconductor surface (520) includes making one or more four-point resistance measurements with an induced current below 100 μ A on the semiconductor surface (520) with a plurality of electrode spacing sets, at least one set having an average spacing below 100 μ m. The sheet resistance and implant leakage is determined through fitting the measured data to theoretical data to within a predetermined error.



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